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(71) Applicant (for all designated States except US):
SILTRONIC AG [DE/DE]; Hanns-Seidel-Platz 4, 81737 München (DE).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **KATO, Hideo** [JP/JP]; 20-2, Kanotouyoucho, Gifu, Gifu 500-8413 (JP). **KYUFU, Shinichi** [JP/JP]; 1-10-22, Iwagari, Hikari, Yamaguchi 743-0051 (JP). **OHKUBO, Masamichi** [JP/JP]; 7-1-14 Mitsui, Hikari, Yamaguchi 743-0011 (JP).(74) Agents: **STAUDACHER, Wolfgang** et al.; SILTRONIC AG, Hanns-Seidel-Platz 4, 81737 München (DE).

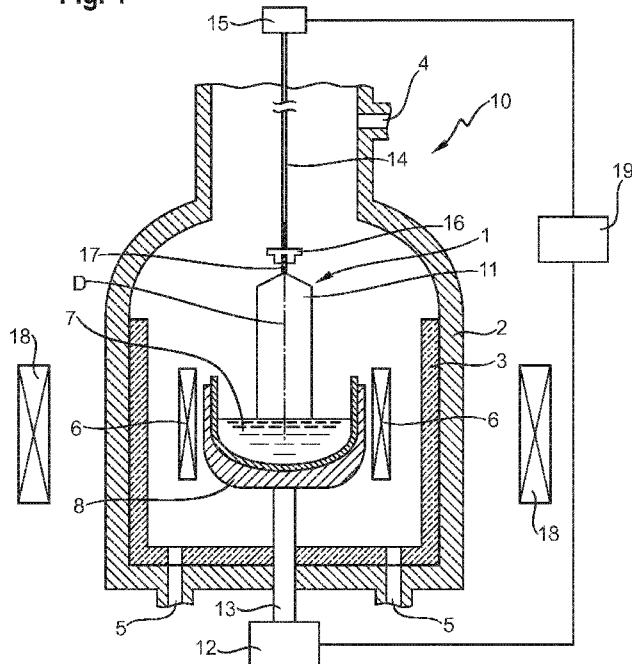
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(54) Title: METHOD FOR MANUFACTURING SINGLE-CRYSTAL SILICON

Fig. 1



(57) Abstract: Subject: There is provided a method for manufacturing single-crystal silicon that makes it possible to reduce occurrence of dislocation of the single-crystal silicon when the single-crystal silicon is grown using a multi-pulling method for pulling up a plurality of pieces of single-crystal silicon from a material melt in an identical crucible. Solving Means: A method for manufacturing single-crystal silicon is directed to a method for manufacturing a single-crystal silicon 1 using the multi-pulling method for pulling up a plurality of pieces of single-crystal silicon 1 from a material melt 7 in an identical crucible 8 within a chamber by a Czochralski method, the method including the step of growing single-crystal silicon 1 in a magnetic field, wherein an amount of addition of barium formed on an inner wall of large-diameter crucible 8 is controlled within a certain range.

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